TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM2GZ47, SM2GZ47A, SM2JZ47, SM2JZ47A

AC POWER CONTROL APPLICATIONS

• IT (RMS) = 1A (Ta = 65°C without radiator)

• Gate Trigger Current: IGT = 5mA Max. (TYPE "A")

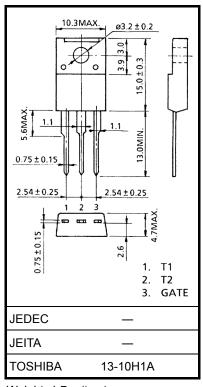
• Repetitive Peak Off-State Voltage: VDRM = 400V, 600V

• R.M.S On-State Current: IT (RMS) = 2A (Tc = 110°C)

• Isolation Voltage: V_{ISOL} = 1500V (AC, t = 60s)

ABSOLUTE MAXIMUM RATINGS

CHARACTER	ISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	SM2GZ47 SM2GZ47A	V	400	V	
	SM2JZ47 SM2JZ47A	V_{DRM}	600	V	
R.M.S On-State Current (Full Sine Waveform)	Tc = 110°C		2	Α	
	Ta = 65°C	IT (RMS)	1		
Peak One Cycle Surge On-State Current (Non-Repetitive)		-	8 (50Hz)	А	
		ITSM	8.8 (60Hz)	A	
I2t Limit Value		I2t	0.32	A2s	
Peak Gate Power Dissipation		P _{GM}	3	W	
Average Gate Power Dissipation		P _G (AV)	0.3	W	
Peak Gate Voltage		V_{FGM}	10	٧	
Peak Gate Current		I _{GM}	1.6	Α	
Junction Temperature		Tj	-40~125	°C	
Storage Temperature F	Range	T _{stg}	-40~125	°C	
Isolation Voltage (AC, t	= 1min.)	V _{ISOL}	1500	V	



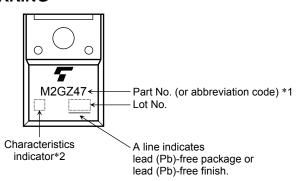
Unit: mm

Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

MARKING

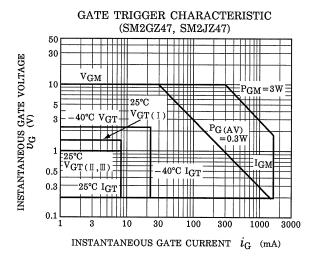


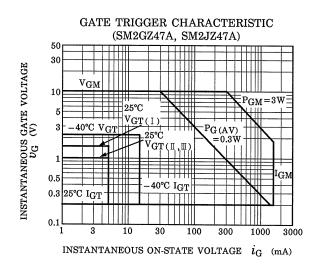
	Part No. (or abbreviation code)	Part No.			
*1	M2GZ47	SM2GZ47, SM2GZ47A			
	M2JZ47	SM2JZ47, SM2JZ47A			
*2 -	Nothing	SM2GZ47, SM2JZ47			
	Α	SM2GZ47A, SM2JZ47A			

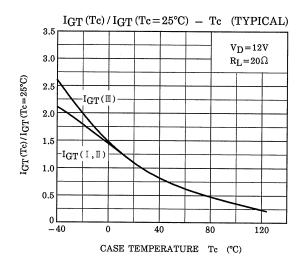


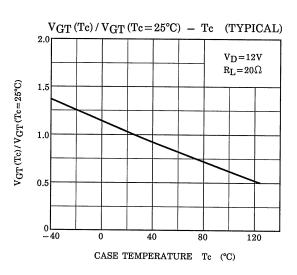
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

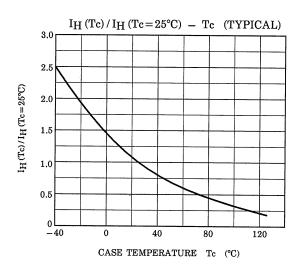
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT	
Repetitive Peak Off-State Current		I _{DRM}	V _{DRM} = Rated		_	_	20	μA	
Gate Trigger Voltage II II IV			V _D = 12V	T2 (+) , Gate (+)	_	_	1.5	V	
				T2 (+) , Gate (-)	_	_	1		
		III	V _{GT}	R _L = 20Ω	T2 (-) , Gate (-)	_	_	1	
		IV			T2 (-) , Gate (+)	_	_	_	
Gate Trigger Current		I	lgт	V _D = 12V R _L = 20Ω	T2 (+) , Gate (+)	_	_	8	- mA
	SM2GZ47 SM2JZ47	II			T2 (+) , Gate (-)	_	_	8	
		III			T2 (-) , Gate (-)	_	_	8	
		IV			T2 (-) , Gate (+)	_	_	_	
	SM2GZ47A SM2JZ47A	I			T2 (+) , Gate (+)	_	_	5	
		II			T2 (+) , Gate (-)	_	_	5	
		III			T2 (-) , Gate (-)	_	_	5	
		IV			T2 (-) , Gate (+)	_	_	_	
Peak On-State Voltage		V _{TM}	I _{TM} = 3A		_	_	1.7	V	
Gate Non-Trigger Voltage		V_{GD}	V _D = Rated, Tc = 125°C		0.2	_	_	V	
Holding Current		l _H	R _L = 100Ω		_	_	10	mA	
Thermal Resistance		R _{th (j−a)}	Junction to Ambient, AC		_	_	55	°C / W	

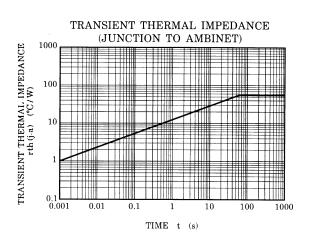


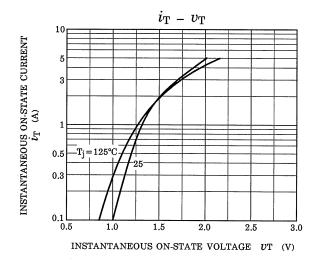


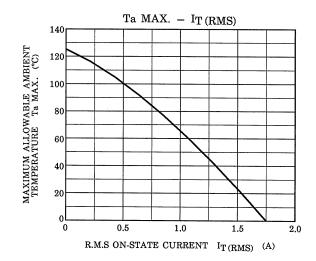












<CONDITION>

- ♦ NO HEAT SINK
- ◆ LEAD FORMING: LB182
- ◆ PRINT BOARD

 $\begin{pmatrix} t = 1.6mm \\ SOLDER LAND : 2mm \phi \end{pmatrix}$

4

RESTRICTIONS ON PRODUCT USE

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which
 manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No
 responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
 may result from its use. No license is granted by implication or otherwise under any patents or other rights of
 TOSHIBA or the third parties.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
 compatibility. Please use these products in this document in compliance with all applicable laws and regulations
 that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
 occurring as a result of noncompliance with applicable laws and regulations.